

isc Silicon NPN Power Transistor

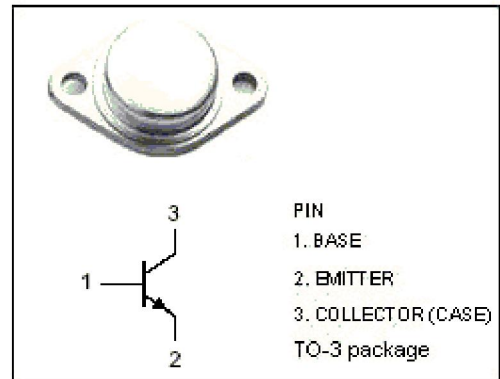
3DD102B

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 150V(\text{Min.})$
- DC Current Gain-
: $h_{FE} = 20(\text{Min.})@I_C = 2A$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 0.8V(\text{Max})@I_C = 2.5A$

APPLICATIONS

- Designed for power amplifier, DC-DC converter and regulated power supply applications.

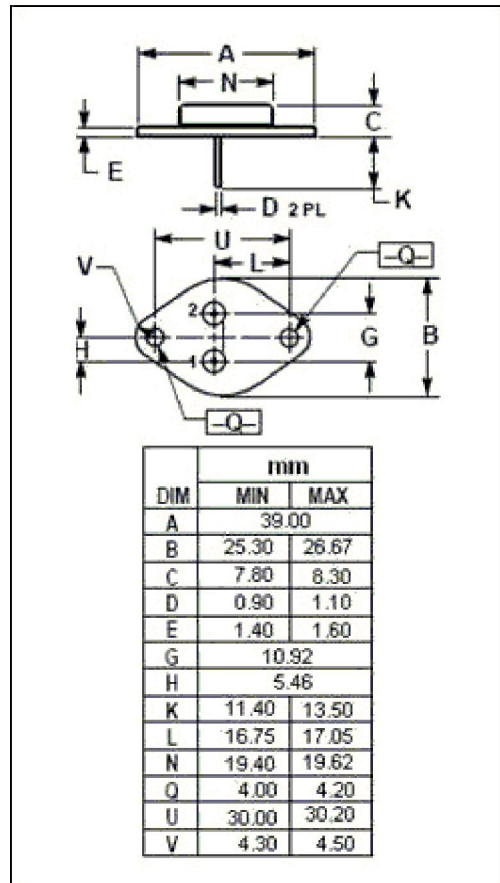


ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current-Continuous	5	A
P_C	Collector Power Dissipation@ $T_C=75^\circ\text{C}$	50	W
T_J	Junction Temperature	175	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~175	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.0	$^\circ\text{C/W}$



isc Silicon NPN Power Transistors**3DD102B****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; I_B=0$	150		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=5\text{mA}; I_E=0$	200		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=5\text{mA}; I_C=0$	4		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.25\text{A}$		0.8	V
I_{CEO}	Collector Cutoff Current	$V_{CE}=50\text{V}; I_B=0$		2.0	mA
I_{CBO}	Collector Cutoff Current	$V_{CB}=50\text{V}; I_E=0$		1.0	mA
h_{FE}	DC Current Gain	$I_C=2\text{A}; V_{CE}=5\text{V}$	20		
f_T	Current Gain-Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=12\text{V}$	1		MHz